

**DLTS measurements on 4H-SiC JBS-diodes with boron implanted local p-n junctions**

Ivanov, Pavel; **Korolkov, Oleg**; Samsonova, Tatyana; **Sleptšuk, Natalja**; Potapov, Alexander; **Toompuu, Jana**; **Rang, Toomas**  
Materials science forum 2011 / p. 409-412 [https://www.researchgate.net/publication/272046403\\_DLTS\\_measurements\\_on\\_4H-SiC\\_JBS-diodes\\_with\\_boron\\_implanted\\_local\\_p-n\\_junctions](https://www.researchgate.net/publication/272046403_DLTS_measurements_on_4H-SiC_JBS-diodes_with_boron_implanted_local_p-n_junctions)

**A DLTS study of 4H-SiC-based p-n junctions fabricated by boron implantation**

Ivanov, Pavel; Potapov, Alexander; Samsonova, Tatyana; **Korolkov, Oleg**; **Sleptšuk, Natalja** Semiconductors 2011 / p. 1306-1310 :  
ill <https://doi.org/10.1134/S1063782611100101>

**Исследование p-n-переходов на основе 4H-SiC, изготовленных имплантацией бора, методом нестационарной емкостной спектроскопии**

Ivanov, Pavel; Potapov, Alexander; Samsonova, Tatyana; **Korolkov, Oleg**; **Sleptšuk, Natalja** Физика и техника полупроводников 2011 / с. 1358-1362 : ил